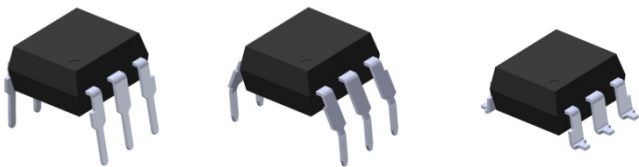


6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER

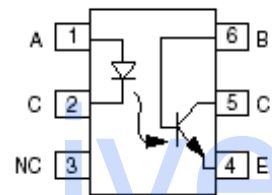
4N2X Series

4N3X Series

H11AX Series



Schematic



Pin Configuration

1. Anode
2. Cathode
3. No Connection
4. Emitter
5. Collector
6. Base

Features:

- 4N2X series: 4N25, 4N26, 4N27, 4N28
- 4N3X series: 4N35, 4N36, 4N37, 4N38
- H11AX series: H11A1, H11A2, H11A3, H11A4, H11A5
- High isolation voltage between input and output (Viso=5000 V rms)
- Creepage distance >7.62 mm
- Operating temperature up to +110°C
- Compact dual-in-line package
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approval
- DEMKO approval
- FIMKO approval
- CSA approved
- CQC approved

Description

The 4N2X, 4N3X, H11AX series of devices each consist of an infrared emitting diode optically coupled to a phototransistor. They are packaged in a 6-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	60	mA
	Peak forward current (t = 10μs)	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation (T _A = 25°C)	P_D	100	mW
	Derating factor (above 100°C)		3.8	mW/°C
Output	Collector-Emitter voltage	V_{CEO}	80	V
	Collector-Base voltage	V_{CBO}	80	V
	Emitter-Collector voltage	V_{ECO}	7	V
	Emitter-Base voltage	V_{EBO}	7	V
	Power dissipation (T _A = 25°C) Derating factor (above 100°C)	P_C	150	mW
	9.0		mW/°C	
	Total Power Dissipation	P_{TOT}	200	mW
	Isolation Voltage* ¹	V_{ISO}	5000	V rms
	Operating Temperature	T_{OPR}	-55 to 110	°C
	Storage Temperature	T_{STG}	-55 to 125	°C
	Soldering Temperature* ²	T_{SOL}	260	°C

Notes:

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3 are shorted together, and pins 4, 5 & 6 are shorted together.

*2 For 10 seconds

Electro-Optical Characteristics (Ta=25°C unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward voltage	V_F	-	1.2	1.5	V	$I_F = 10\text{mA}$
Reverse current	I_R	-	-	10	μA	$V_R = 6\text{V}$
Input capacitance	C_{in}	-	30	-	pF	$V = 0, f = 1\text{MHz}$

Output

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Collector-Base dark current	I_{CBO}	-	-	20	nA	$V_{CB} = 10\text{V}$
Collector-Emitter dark current	4N2X	-	-	50	nA	$V_{CE} = 10\text{V}, I_F = 0\text{mA}$
	H11AX	-	-	50		
	4N3X	-	-	50		
Collector-Emitter breakdown voltage	BV_{CEO}	80	-	-	V	$I_C = 1\text{mA}$
Collector-Base breakdown voltage	BV_{CBO}	80	-	-	V	$I_C = 0.1\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	$I_E = 0.1\text{mA}$
Emitter-Base breakdown voltage	BV_{EBO}	7	-	-	V	$I_E = 0.1\text{mA}$
Collector-Emitter capacitance	C_{CE}	-	8	-	pF	$V_{CE} = 0\text{V}, f = 1\text{MHz}$

* Typical values at $T_a = 25^\circ\text{C}$

Transfer Characteristics

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Current Transfer ratio	4N35, 4N36, 4N37	100	-	-	%	$I_F = \pm 10\text{mA}, V_{CE} = 10\text{V}$
	H11A1	50	-	-		
	H11A5	30	-	-		
	4N25, 4N26, 4N38, H11A2, H11A3	20	-	-		
	4N27, 4N28, H11A4	10	-	-		
Collector-Emitter saturation voltage	4N25, 4N26, 4N27, 4N28	-	-	0.5	V	$I_F = 50\text{mA}, I_C = 2\text{mA}$
	4N35, 4N36, 4N37	-	-	0.3		
	H11A1, H11A2, H11A3, H11A4, H11A5	-	-	0.4		$I_F = 10\text{mA}, I_C = 0.5\text{mA}$
	4N38	-	-	1.0		
Isolation resistance	R_{IO}	10^{11}	-	-	Ω	$V_{IO} = 500\text{Vdc}$
Input-output capacitance	C_{IO}	-	0.2	-	pF	$V_{IO} = 0, f = 1\text{MHz}$
Turn-on time	4N25, 4N26, 4N27, 4N28, H11A1, H11A2, H11A3, H11A4, H11A5	-	3	10	μs	$V_{CC} = 10\text{V}, I_F = 10\text{mA}, R_L = 100\Omega$ See Fig. 11
	4N35, 4N36, 4N37, 4N38	-	10	12		
Turn-off time	4N25, 4N26, 4N27, 4N28, H11A1, H11A2, H11A3, H11A4, H11A5	-	3	10	μs	$V_{CC} = 10\text{V}, I_F = 10\text{mA}, R_L = 100\Omega$ See Fig. 11
	4N35, 4N36, 4N37, 4N38	-	9	12		

* Typical values at $T_a = 25^\circ\text{C}$

Typical Electro-Optical Characteristics Curves

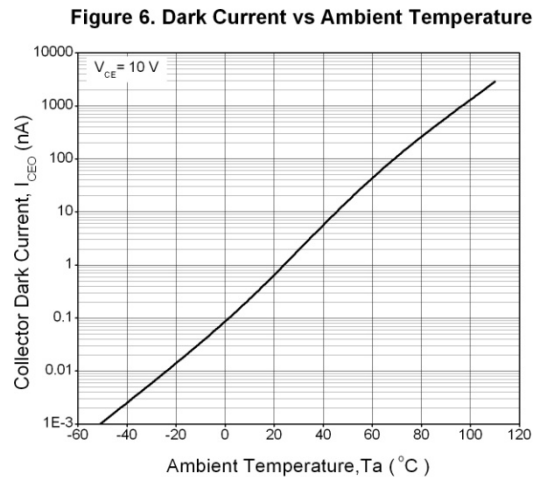
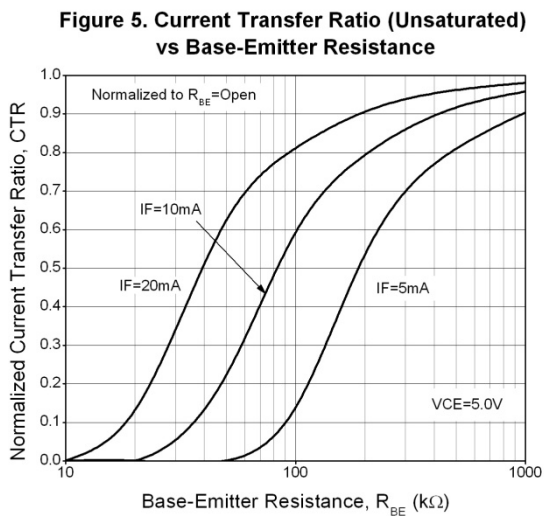
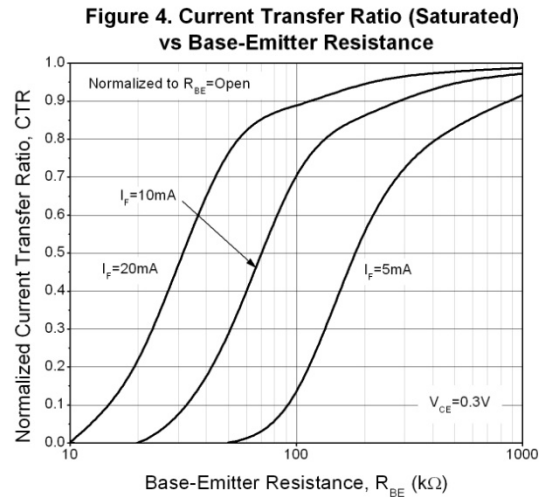
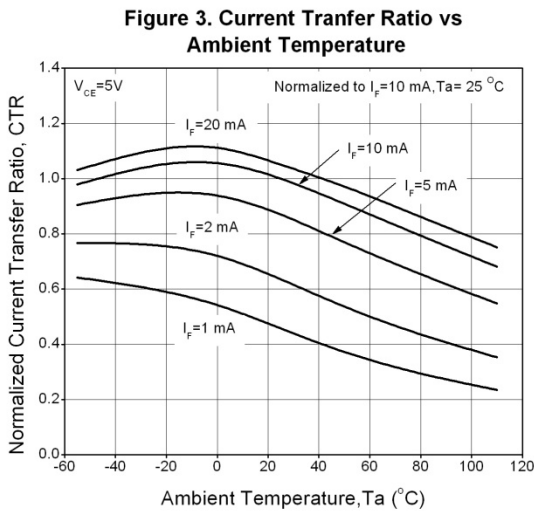
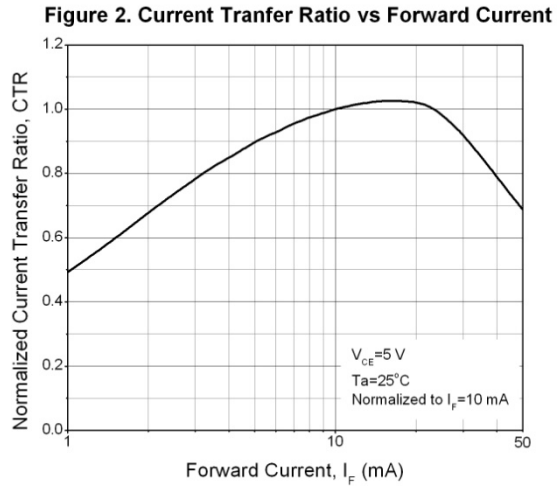
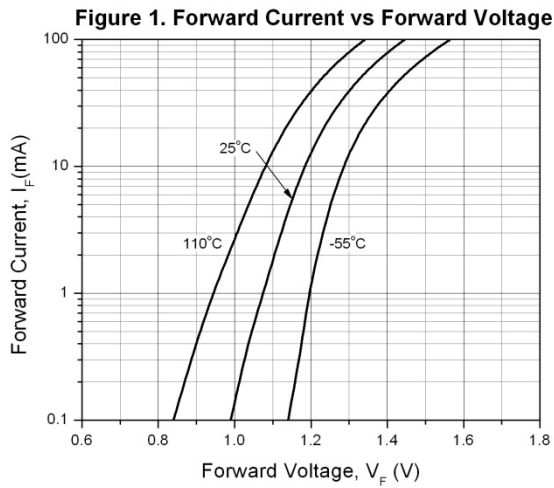


Figure 7. Collector-Emitter Saturation Voltage vs Collector Current

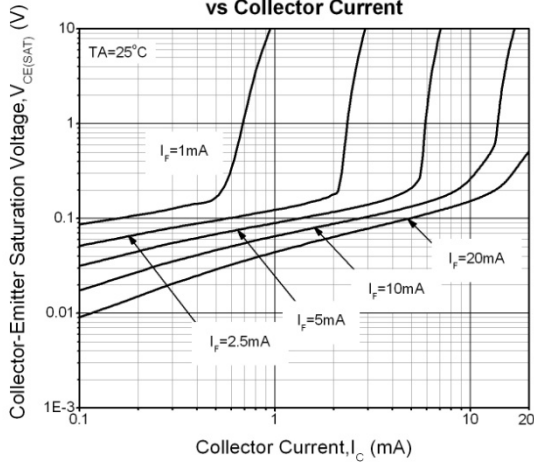


Figure 8. Switching Time vs Load Resistance

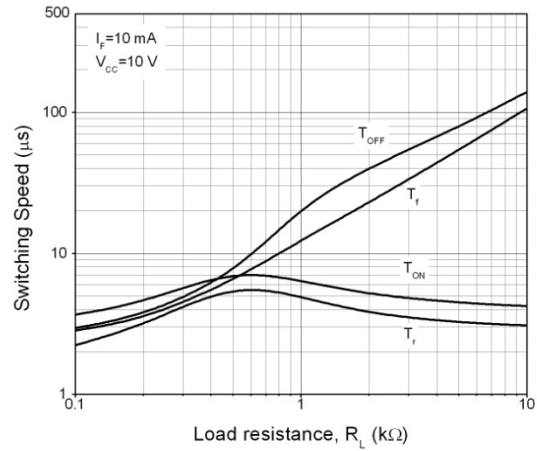


Figure 9. Turn-on Time vs Base-Emitter Resistance

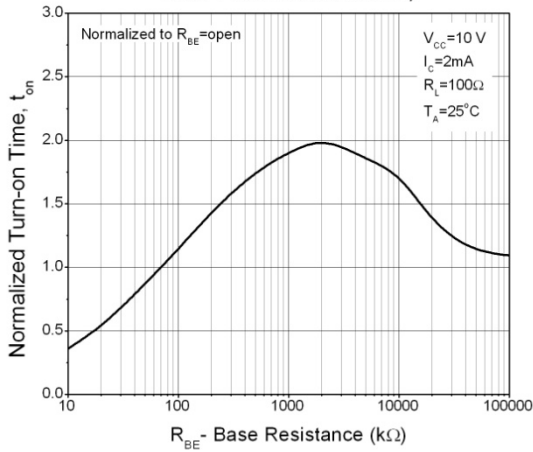


Figure 10. Turn-off Time vs Base-Emitter Resistance

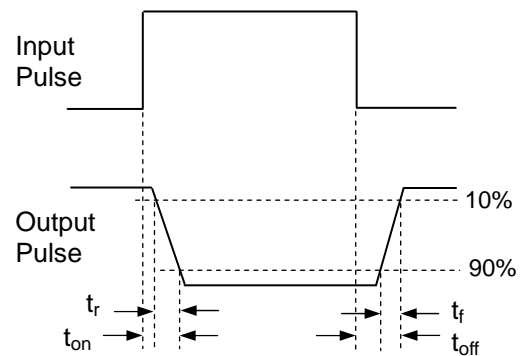
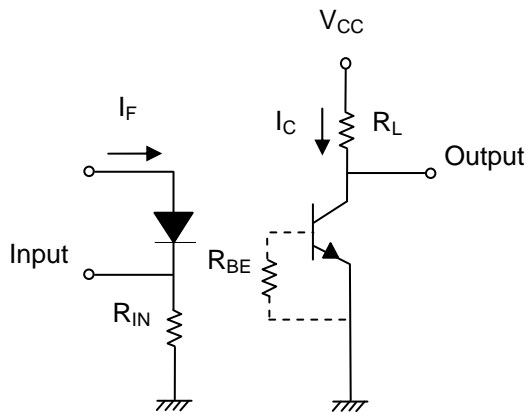
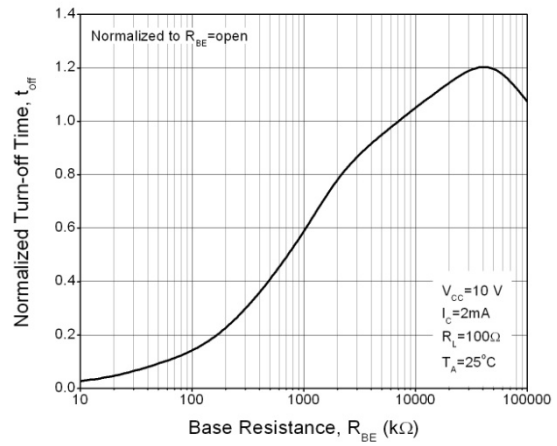


Figure 11. Switching Time Test Circuit & Waveforms

Order Information

Part Number

4NXXY(Z)-V

or

H11AXY(Z)-V

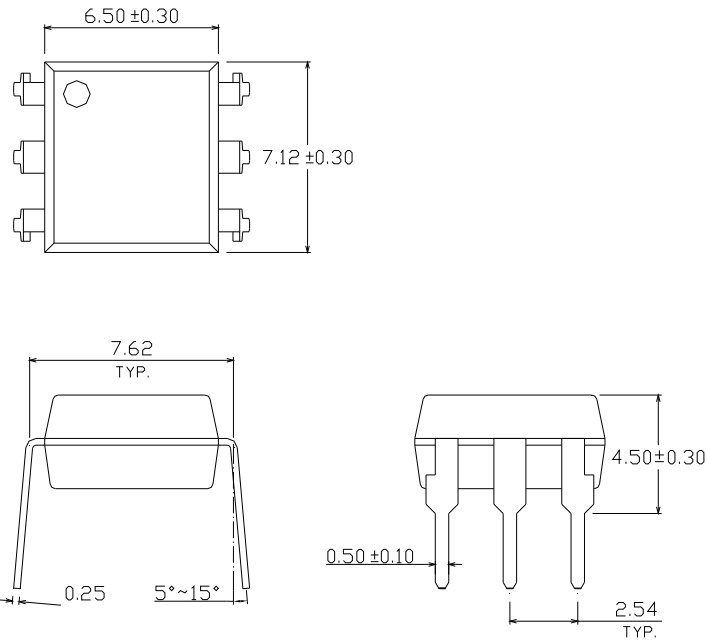
Note

- XX = Part no. for 4NXX series (25, 26, 27, 28, 35, 36, 37 or 38)
- X = Part no. for H11AX series (1, 2, 3, 4, or 5)
- Y = Lead form option (S, S1, M or none)
- Z = Tape and reel option (TA, TB or none).
- V = VDE safety (optional)

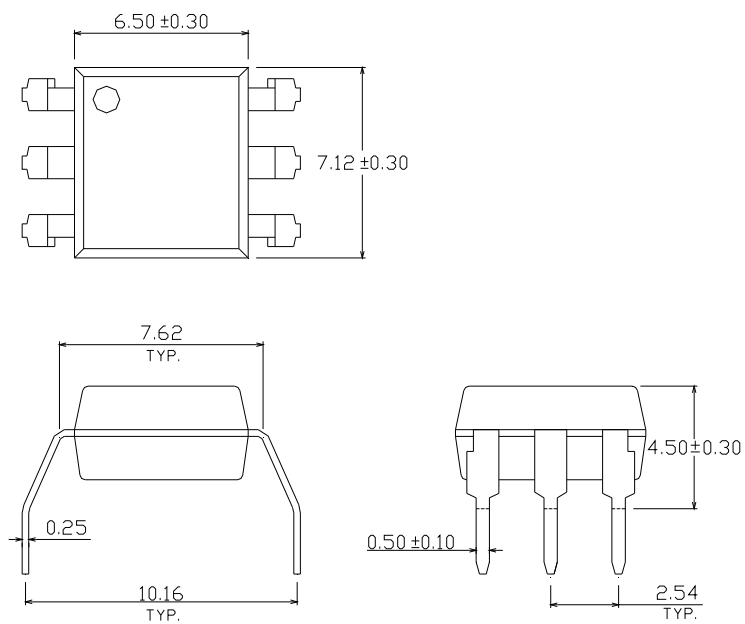
Option	Description	Packing quantity
None	Standard DIP-6	65 units per tube
M	Wide lead bend (0.4 inch spacing)	65 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

Package Dimension (Dimensions in mm)

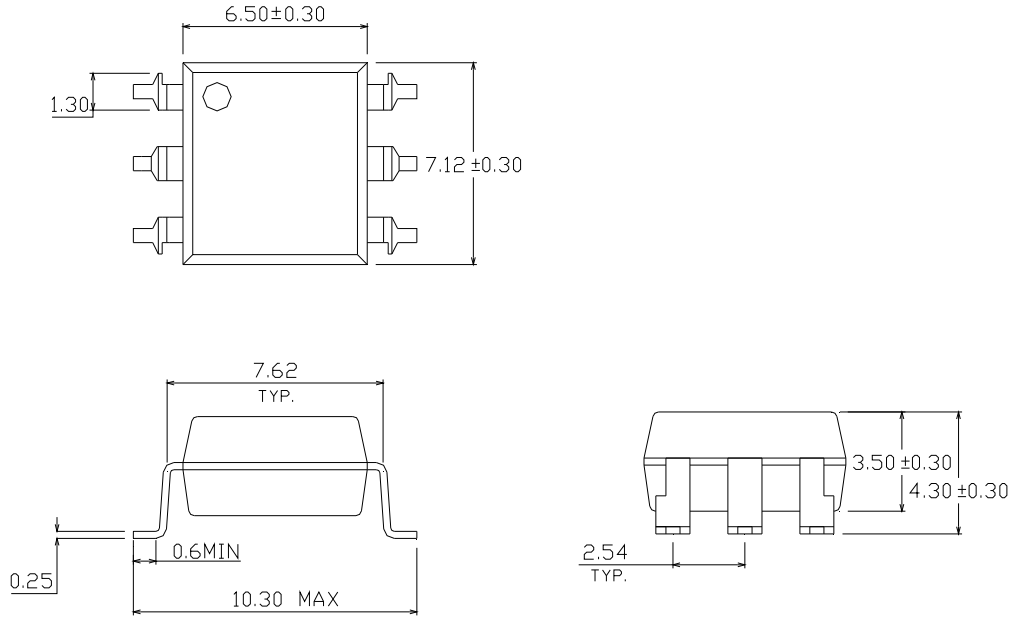
Standard DIP Type



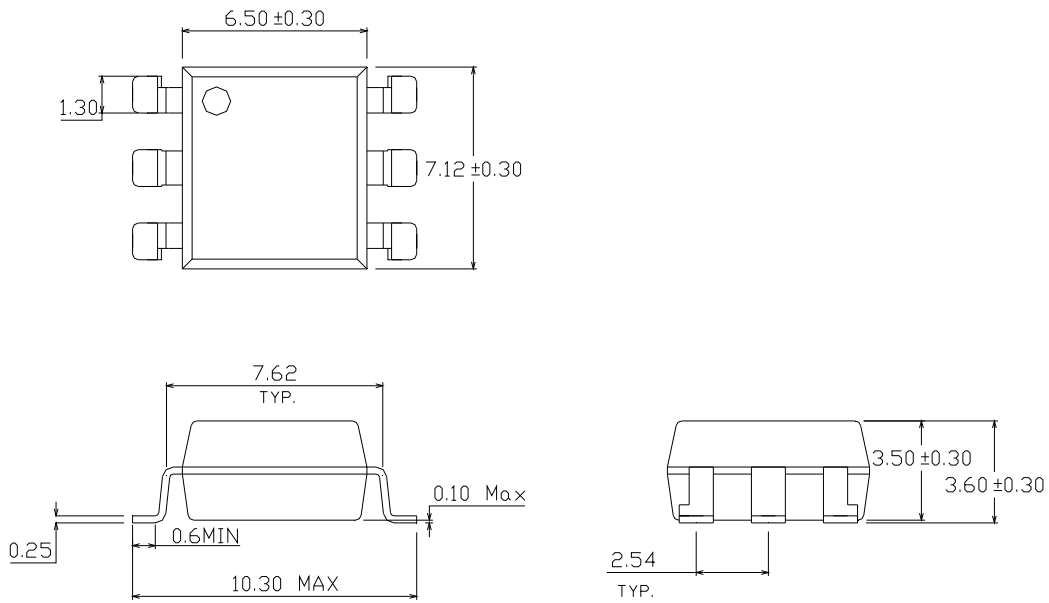
Option M Type



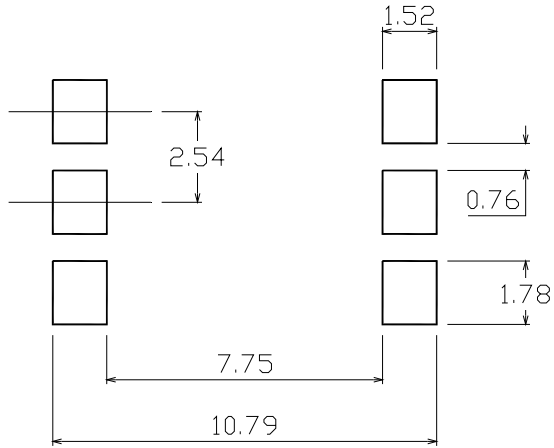
Option S Type



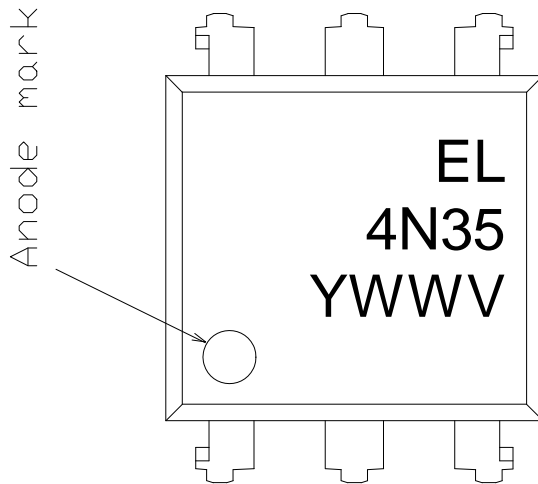
Option S1 Type



Recommended pad layout for surface mount leadform



Device Marking

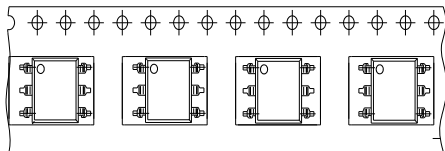


Notes

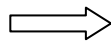
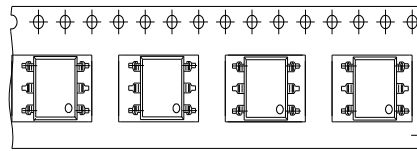
- EL denotes Everlight
- 4N35 denotes Device Number
- Y denotes 1 digit Year code
- WW denotes 2 digit Week code
- V denotes VDE (optional)

Tape & Reel Packing Specifications

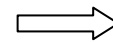
Option TA



Option TB

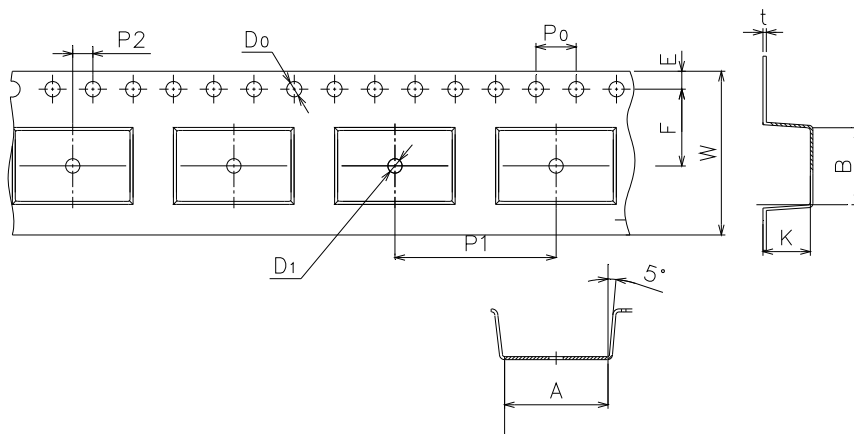


Direction of feed from reel



Direction of feed from reel

Tape dimensions

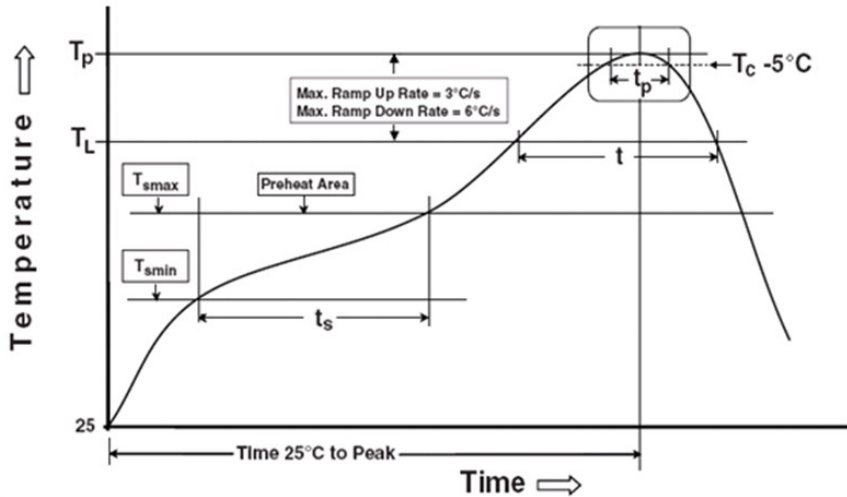


Dimension No.	A	B	Do	D1	E	F
Dimension (mm)	10.4±0.1	7.5±0.1	1.5±0.1	1.5+0.1/-0	1.75±0.1	7.5±0.1
Dimension No.	Po	P1	P2	t	W	K
Dimension (mm)	4.0±0.15	12±0.1	2.0±0.1	0.35±0.03	16.0±0.2	4.5±0.1

Precautions for Use

1. Soldering Condition

1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note:

Reference: IPC/JEDEC J-STD-020D

Preheat

Temperature min (T_{smin})	150 °C
Temperature max (T_{smax})	200°C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max

Other

Liquidus Temperature (T_L)	217 °C
Time above Liquidus Temperature (t_L)	60-100 sec
Peak Temperature (T_p)	260°C
Time within 5 °C of Actual Peak Temperature: $T_p - 5^\circ\text{C}$	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max.
Time 25°C to peak temperature	8 minutes max.
Reflow times	3 times

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